

# SANYO Semiconductors DATA SHEET

# LA5663V — Phase Control Voltage Inverter Control IC

#### **Overview**

The LA5663V is Phase Control Voltage Inverter Control IC.

#### **Functions**

- Phase control technique allows the voltage transformer to be driven at a frequency that provides excellent efficiency.
- The phase can be adjusted with an external resistor.
- Allows burst adjustment.
- Full complement of built-in protection circuits, including over-voltage protection and tube current detection and protection.
- High-precision reference voltage system. VREM precision: ±1%
- The on/off state of the VREM circuit can be controlled independent.

# **Specifications**

#### **Maximum Ratings** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage	V <sub>CC</sub>		24	V
Maximum power drain allowed	Pd max	Independent IC.	440	mW
Operating temperature range	Topr		-30 to 85	°C
Storage temperature range	Tstg		-55 to 150	°C

#### **Operating Conditions** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Input voltage	V <sub>CC</sub>		4.5 to 23	V
Oscillation frequency	fosc		40 to 500	kHz
Burst drive frequency	<sup>f</sup> PWM		50 to 1000	Hz
Output drive load capacity	CL1		0 to 1000	pF
	CL2		0 to 1000	pF

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# Electrical Characteristics at Ta = $25^{\circ}$ C, V<sub>CC</sub> = 15.0V

Description			Conditions	Ratings			
Pa	arameter	Symbol	Conditions	min	typ	max	Unit
Current drain during standby		loff				5	μA
Current drain during operation		Іор	V <sub>CC</sub> = 23V, DTC = 1.229V, CL = 500pF	8	11	14	mA
Regulator voltage		Vreg	V <sub>CC</sub> = 4.5 to 23V, Ireg = 0 to 0.5mA	3.395	3.5	3.605	V
Regulator temperatu	ure coefficient	Vreg (T)	Ireg = 0.5mA, Ta = 0 to 60°C		0.23		%
Regulator current		Ireg		-0.3		2	mA
Reference voltage		Vref	$V_{CC}$ = 4.5 to 23V, Iref = 0 to 0.1mA	1.972	2	2.028	V
Reference voltage to	emperature coefficient	Vref (T)	Iref = 0.1mA, Ta = 0 to 60°C		0.23		%
Reference voltage c	urrent	Iref		0		0.2	mA
p-channel		Voph1	Relative to $V_{CC}$ , load current of 0mA.	-0.4			V
output voltage		Voph2	Relative to $V_{CC}$ , load current of 10mA.	-1.2			V
	"I " Joy of	Vopl1	Relative to GND, load current of 0mA.			1.3	V
	Lievei	Vopl2	Relative to GND, load current of 10mA.			1.4	V
	Clamp level	Vopc	Relative to $V_{CC}$	-12	-10	-8	V
	tr	trp	CL = 500pF		150		ns
	tf	tfp	CL = 500pF		200		ns
n-channel		Vonh1	Relative to V <sub>CC</sub> , load current of 0mA.	-1.5			V
output voltage	"H" level	Vonh2	Relative to V <sub>CC</sub> , load current of 10mA.	-2			V
		Vonl1	Relative to GND, load current of 0mA.			0.4	V
	"L" level	Vonl2	Relative to GND, load current of 10mA.			1.2	V
	Clamp level	Vopc	Relative to V <sub>CC</sub>	8	10	12	V
	tr	trn	CL = 500pF		650		ns
	tf	tfn	CL = 500pF		50		ns
Burst drive duty	BRIGHT_VR = 2.2V	Duty1	V <sub>CC</sub> = 4.5 to 23V	100			%
	BRIGHT_VR = 1.847V	Duty2	V <sub>CC</sub> = 4.5 to 23V	86	90	94	%
	BRIGHT_VR = 1.229V	Duty3	V <sub>CC</sub> = 4.5 to 23V	47	50	53	%
	BRIGHT_VR = 0.618V	Duty4	V <sub>CC</sub> = 4.5 to 23V	7	10	13	%
	BRIGHT_VR = 0.4V	Duty5	$V_{CC} = 4.5 \text{ to } 23 \text{V}$			0	%
Burst drive duty	BRIGHT_VR = 2.2V	Duty1 (T)	Ta = 0 to 60°C		0		%
temperature	BRIGHT_VR = 1.847V	Duty2 (T)	Ta = 0 to 60°C		2		%
coefficient	BRIGHT_VR = 1.229V	Duty3 (T)	Ta = 0 to 60°C		2		%
	BRIGHT_VR = 0.618V	Duty4 (T)	Ta = 0 to 60°C		2		%
	BRIGHT_VR = 0.4V	Duty5 (T)	Ta = 0 to 60°C		0		%
Oscillation	fmax	fosc1	capacity = ±1%	247	258	269	kHz
frequency	fmin	fosc2	capacity = $\pm 1\%$	195	202	209	kHz
Oscillation	fmax (T)	fosc1 (T)	Ta = 0 to 60°C		1.3		%
frequency	fmin (T)	fosc2 (T)	Ta = 0 to 60°C		1.3		%
temperature							
coefficient		facat	apposity = 11%	101	202	212	<u>ц</u> ,
Burst drive frequency		face1	$T_{2} = 0 \text{ to } C^{2}C$	191	202	213	
Burst drive frequency temperature coefficient		IUSCI	1a = 0 10 60°C	2	0.64		% 
Remote voltage		Viemon		2		0.7	V
Stopped		Viemon		0.07	0.00	0.7	v ,,
OPT output			$v_{CC} = 22v$	0.27	0.32	0.37	V
				1.557	1.6	1.643	V
				100			μA
		-vcon_sour	-VCOM source current	10			μA
DIC-100% ON three	snold voltage	V100		2.16	2.2	2.24	V
DIC-100% OFF three	esnold voltage	VO	000	0.392	0.4	0.408	V
307	Operation start time	tscp	SCP capacity = 0.33µF	0.7	1	1.5	S
	Threshold voltage	SCP (DET_CR)		0.23	0.26	0.29	V

Decompter	Querra ha al		Ratings			
Parameter	Symbol	Conditions	min	typ	max	Unit
Input pin						
Input current of V_PHASE pin	IVPHASE		-0.2		0.2	μA
Input current of BRIGHT_VR pin	IBRIGHT_VR		-0.2		0.2	μA
Current of DTC	IVPHASE		-0.2		0.2	μΑ

# **Package Dimensions**

unit: mm

3175C





# **Pin Assignment**





# **Block Diagram and Application Circuit Example**

# **Pin Functions**

Pin No.	Pin name	Function	Equivalent circuit
1	VREM	ON/OFF terminal of the IC.	
2	SGND	Signal Ground terminal.	
3	IFB	CCFL electric current waveform input terminal.	
4	DET_CR	Rectification (pulse way) waveform of CCFL output terminal.	IFB O 30kΩ DET_CR O 30kΩ SGND
5	VLOOP_C	Error amplifier output terminal.	VLOOP_C O
6	RECT_C	Phase difference output terminal	VCC OVREG RECT_C OVREG
7	V_PHASE	Phase difference setup terminal	V <sub>CC</sub> O VREG VREG V_ V_PHASE V_PHASE SGND

Din No.	Din nome	Eurotion	Equivalant aircuit
P III INU. 9			
0	TLOOF_C		VCC VREG
9	C_PWM	Capacitor terminal for the burst drive frequency setup.	VCC VCC VCC VCC VCC VCC VCC VCC
10	R_PWM	Resistance terminal for the burst drive frequency setup.	VCC OVREG
11	BRIGHT_VR	Burst width set up terminal.	VCC VREG VREG VREG SOUD SGND
12	OVP	Detection input terminal of over voltage protection circuit.	V <sub>CC</sub> · · · · · · · · · · · · · · · · · ·

Continued	from preceding page.		
Pin No.	Pin name	Function	Equivalent circuit
13 14	N_GATE1 N_GATE2	NchMOS drive terminal. NchMOS drive terminal.	N_GATE* O VCC
15	PGND	Power ground terminal.	
16	P_GATE	PchMOS drive terminal.	P_GATE O VCC
17	VCC	Power supply terminal.	
18	-VCON	Output voltage is inversely proportional to V <sub>CC</sub> .	80.942kΩ ····································
19	SCP	Time constant of short protection circuit setup terminal.	V <sub>CC</sub> V <sub>CC</sub> V <sub>CC</sub> V <sub>CC</sub> V <sub>REG</sub> V <sub>CC</sub> V <sub>REG</sub> SCP V <sub>REG</sub> SCP

Pin No.	Pin name	Function	Equivalent circuit
20	DTC	Dead time setup terminal.	
			DTC OVREG
21	c_osc	Capacitor terminal for the VCO frequency setup.	VREG O
22	R_OSC	Resistance terminal for the VCO frequency setup.	V <sub>CC</sub> VREG
23	VREF	Standard voltage output terminal.	VCC VCC VCC VREF VSC VREF VSC VREF VSC VREF VSC VSC VSC VSC VSC VSC VSC VSC VSC VSC
24	VREG	Regulator voltage output terminal.	VCC VCC VREG VREG VREG VREG VREG VREG VREG VREG

# **Functional Descriptions**

# (1) IFB and DET\_CR pins

The IFB pin connects the CCFL current waveform detected by R10 to the Q4 base with bias VBE. The DET\_CR pin output level depends on both the Q4 base voltage less the VF component and the time constant determined by C4 and R2. These connections rectify the AC CCFL current waveform (VAC) for input to the negative side of the ERROR amplifier.



(2) VLOOP\_C and PGATE pins

The PWM waveform output from the P\_GATE pin is the result of the PWM1 amplifier comparing the VLOOP\_C voltage and the VOC triangular wave so that the rectified CCFL current waveform from the DET\_CR pin has the same potential (0.5V) as the positive side of the ERROR amplifier. This PWM control ensures that the CCFL current remains constant.



# (3) RECT\_C pin

COMP1 rectifies the CCFL current waveform, plus bias VBE, from the IFB pin. ANDing this waveform voltage with that from point A (this latter has the same phase as NGATE2) averages the two, producing phase difference voltage output from the RECT\_C pin.



# (4) V\_PHASE and FLOOP\_C pins

COMP2 controls the VCO frequency so that the RECT\_C and V\_PHASE pins have the same voltage. The RECT\_C pin voltage represents a phase difference voltage, so changing the V\_PHASE pin voltage adjusts the phase difference.



\* The above graph is based on measurements for the IC in isolation. Actual phase difference adjustment requires connection to the piezoelectric transformer.

# (5) C\_OSC and R\_OSC pins

These inputs determine the VCO oscillation frequency. Use R\_OSC to change the basic frequency.



(6) C\_PWM, R\_PWM, and BRIGHT\_VR pins

These inputs determine the burst drive frequency. Use the BRIGHT\_VR pin voltage to change the burst width and R\_PWM to change the burst drive frequency.



\* The above graph is based on measurements for the independent IC.

# (7) –VCON and DTC pins

The –VCON pin output voltage is inversely proportional to V<sub>CC</sub>. Using this output to create the DTC pin input voltage specifies a maximum duty dependent on V<sub>CC</sub>. On the other hand, connecting this output to the V\_PHASE pin input via the resistances R14 and R15 specifies a phase setting dependent on V<sub>CC</sub>. (Eliminate resistances R14 and R15 if such a V<sub>CC</sub>-dependent phase setting is not necessary.)

\* The Specifications stipulate OP1 output electrical characteristics for the -VCON pin.



# (8) N\_GATE1 and N\_GATE2 pins

These pins drive the n-channel MOSFET. The frequency is 1/4 the VCO frequency.



#### (9) VREM pin

This input turns the IC on and off. Turning the IC off reduces the current drain to  $5\mu A$  or less.



# (10) OVP

This is the over-voltage detection terminal.

An OVP terminal gains a voltage that is divided by resistances. It works with threshold voltage 2V. It becomes the condition of the table at the time of the movement.

Terminal	Condition
P_GATE	Hi
VLOOP_C	Low
FLOOP_C	Low
N_GATE1, 2	Drive

And once over-voltage protection works, it doesn't revert soon even if OVP is lower than 2V again. It reverts after fixed time (the period of C\_PWM) passes.



#### (11) SCP

CCFL electric current decrease by the CCFL opening and so on. And a charge begins in the condenser connected to SCP when the voltage of DET\_CR was less than 0.26V.

Latch is set when the voltage of the condenser is more than 2V. The voltage of each terminal at this time becomes a table.

The charge of the condenser is stopped in the burst Duty again at the time of off period.

Terminal	Condition
P_GATE	Hi
VLOOP_C	Low
FLOOP_C	Low
N_GATE1, 2	Low

tscp =  $3.03 \times 10^6 \times C14 \times (100/burst duty)$  [S] Example: tscp = 1 [S] (At C14 =  $0.33 \mu$ F, burst duty = 100%)



#### (12) The polarity of the piezoelectric transformer

You must put logic with the transformer together, because a phase is controlled by comparing the common mode wave shape of  $N_GATE2$  with the common mode wave shape of CCFL electric current.

Connect a piezoelectric transformer so that each wave shape may become relations like a figure.



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